

# **DATA SHEET**



# MOS FIELD EFFECT TRANSISTOR 2SJ598

# SWITCHING P-CHANNEL POWER MOS FET

#### **DESCRIPTION**

The 2SJ598 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

#### **FEATURES**

• Low on-state resistance:

 $R_{DS(on)1}$  = 130 m $\Omega$  MAX. (Vgs = -10 V, ID = -6 A)

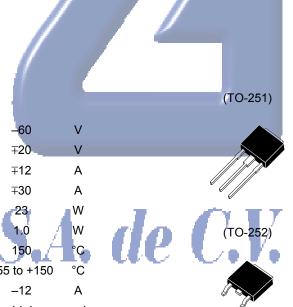
- $R_{DS(on)2} = 190 \text{ m}\Omega \text{ MAX.} \text{ (V}_{GS} = -4.0 \text{ V}, I_D = -6 \text{ A)}$
- Low Ciss: Ciss = 720 pF TYP.
- Built-in gate protection diode
- TO-251/TO-252 package

## ABSOLUTE MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Drain to Source Voltage (VGS = 0 V)	VDSS	-60	V
Gate to Source Voltage (VDS = 0 V)	Vgss	∓20	V
Drain Current (DC) (Tc = 25°C)	I <sub>D(DC)</sub>	∓12	Α
Drain Current (pulse) Note1	I <sub>D(pulse)</sub>	∓30	Α
Total Power Dissipation (Tc = 25°C)	Рт	23	W
Total Power Dissipation (T <sub>A</sub> = 25°C)	PTT	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	-12	Α
Single Avalanche Energy Note2	Eas	14.4	mJ

### ★ ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ598	TO-251 (MP-3)
2SJ598-Z	TO-252 (MP-3Z)



**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

2. Starting T<sub>ch</sub> = 25°C, V<sub>DD</sub> = -30 V, R<sub>G</sub> = 25  $\Omega$ , V<sub>GS</sub> = -20  $\rightarrow$  0 V

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